



60V P-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

Product Summary

BV _{DSS}	R _{DS(ON)} Max	I _D Max T _C = +25°C
201/	60mΩ @ V _{GS} = -10V	-18.8A
-60V	80mΩ @ V _{GS} = -4.5V	-16.8A

Features and Benefits

- 100% Unclamped Inductive Switch (UIS) Test in Production
- Low RDS(ON) Ensures Minimal On-State Losses
- Wettable Flank for Improved Optical Inspection
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The DMP6051SFVWQ is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF 16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Description and Applications

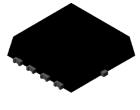
This MOSFET is designed to meet the stringent requirements of automotive applications. It is qualified to AEC-Q101, supported by a PPAP, and is ideal for use in:

- Motor controls
- Power-management functions
- DC-DC converters

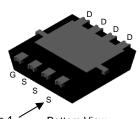
Mechanical Data

- Package: PowerDI®3333-8
- Package Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.03 grams (Approximate)

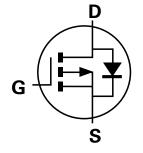








Pin 1 **Bottom View**



Equivalent Circuit

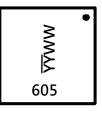
Ordering Information (Note 4)

Orderable Part Number	Dockers	Packing		
Orderable Part Number	Package	Qty.	Carrier	
DMP6051SFVWQ-7	PowerDI3333-8/SWP (Type UX)	2000	Tape & Reel	
DMP6051SFVWQ-13	PowerDI3333-8/SWP (Type UX)	3000	Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



605 = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 24 = 2024) WW = Week Code (01 to 53)



Maximum Ratings (@ $T_A = +25$ °C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V_{DSS}	-60	V	
Gate-Source Voltage		Vgss	±20	V
Continuous Drain Current (Note 6) V _{GS} = -10V	Tc = +25°C Tc = +70°C	ΙD	-18.8 -15.1	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ідм	-75	Α	
Maximum Continuous Body Diode Forward Current (Note 6)	Is	-20.6	Α	
Pulsed Source Current (10µs Pulse, Duty Cycle = 1%)		lsм	-75	Α
Avalanche Current, L = 0.1mH		las	-27	Α
Avalanche Energy, L = 0.1mH		E _{AS}	36	mJ

Thermal Characteristics ($@T_A = +25^{\circ}C$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Total Power Dissipation (Note 5)	PD	2.7	W
Thermal Resistance, Junction to Ambient (Note 5)	Reja	47	°C/W
Total Power Dissipation (Note 6)	PD	43	W
Thermal Resistance, Junction to Case (Note 6)	Rejc	2.9	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BVDSS	-60	_	_	V	$V_{GS} = 0$, $I_{D} = -250\mu A$	
Zero Gate Voltage Drain Current	IDSS	_	_	-1	μΑ	V _{DS} = -60V, V _{GS} = 0	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0$	
ON CHARACTERISTICS (Note 7)	•						
Gate Threshold Voltage	Vgs(TH)	-1	_	-3	V	$V_{DS} = V_{GS}$, $I_D = -250\mu A$	
Static Drain-Source On-Resistance	Dagger	_	48	60	mΩ	$V_{GS} = -10V, I_{D} = -7A$	
Static Drain-Source On-Resistance	RDS(ON)	_	62	80	11122	V _G S = -4.5V, I _D = -7A	
Diode Forward Voltage	V _{SD}	_	-0.8	-1.2	V	V _{GS} = 0, I _S = -1A	
DYNAMIC CHARACTERISTICS (Note 8)						•	
Input Capacitance	Ciss		2087	_	pF		
Output Capacitance	Coss	_	94	_	pF	V _{DS} = -30V, V _{GS} = 0, - f = 1MHz	
Reverse Transfer Capacitance	Crss	_	78	_	pF I = IMH2		
Gate Resistance	Rg	_	3.5	_	Ω	$V_{DS} = 0$, $V_{GS} = 0$, $f = 1MHz$	
Total Gate Charge (V _{GS} = -4.5V)	Qg	_	17	_	nC		
Total Gate Charge (V _{GS} = -10V)	Qg	_	36	_	nC	\/ 20\/ I 5A	
Gate-Source Charge	Qgs	_	3.7	_	nC	$V_{DS} = -30V, I_{D} = -5A$	
Gate-Drain Charge	Qgd	_	5.6	_	nC	1	
Turn-On Delay Time	t _{D(ON)}		6.5	_	ns		
Turn-On Rise Time	t _R	_	19	_	ns	$V_{DD} = -30V, V_{GS} = -10V,$ $R_{G} = 3\Omega, I_{D} = -5A$	
Turn-Off Delay Time	tD(OFF)		40	_	ns		
Turn-Off Fall Time	tF	_	24	_	ns		
Body Diode Reverse-Recovery Time	t _{RR}	_	23	_	ns	I 5A 31/34 400A/	
Body Diode Reverse-Recovery Charge	Q _{RR}	_	21	_	nC	$\frac{1}{1}$ IF = -5A, di/dt = 100A/µs	

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.

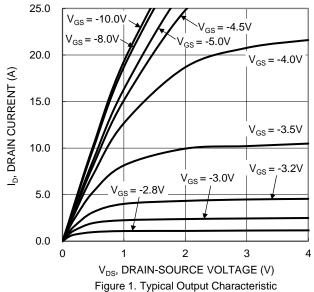
6. Thermal resistance from junction to soldering point (on the exposed drain pad).

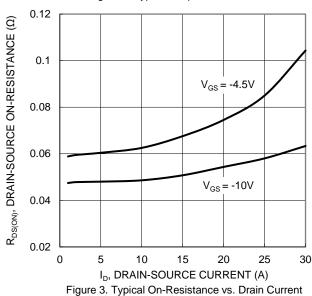
7. Short duration pulse test used to minimize self-heating effect.

8. Guaranteed by design. Not subject to product testing.









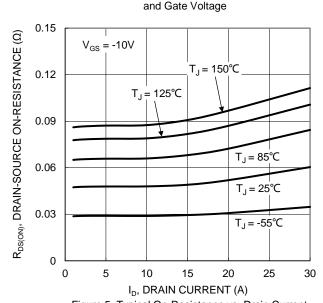
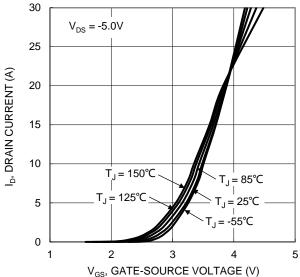
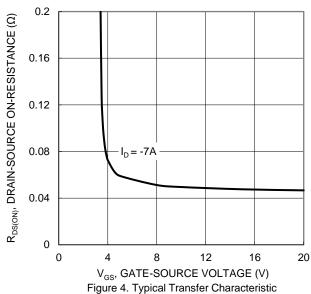


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature



V_{GS}, GATE-SOURCE VOLTAGE (V) Figure 2. Typical Transfer Characteristic



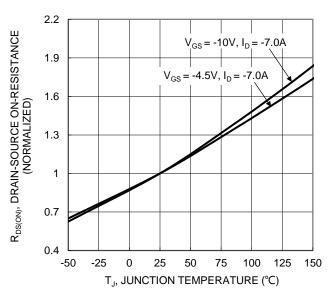


Figure 6. On-Resistance Variation with Junction Temperature



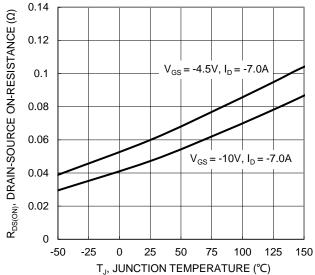


Figure 7. On-Resistance Variation with Junction Temperature

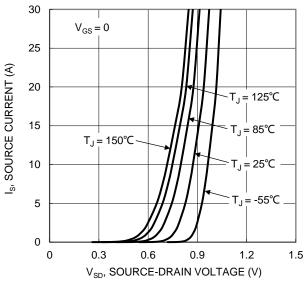


Figure 9. Diode Forward Voltage vs. Current

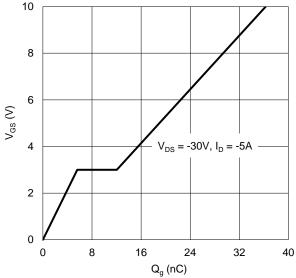


Figure 11. Gate Charge

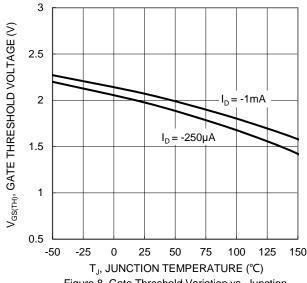
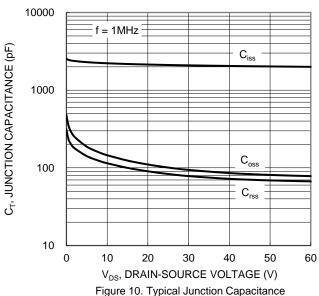


Figure 8. Gate Threshold Variation vs. Junction Temperature



1000 $R_{DS(ON)}$ Limited 100 ID, DRAIN CURRENT (A) 10 = 10µs $P_W = 100 \mu s$ T_{J(Max)} = 150°C Single Pulse $P_W = 10ms$ DUT on Infinite $P_{w} = 100 ms$ Heatsink $V_{GS} = -10V$ 0.1 10 100 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area



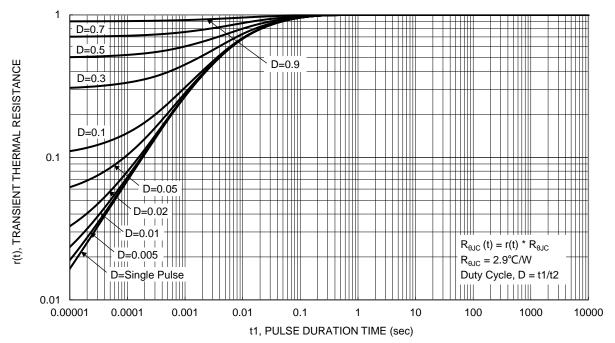


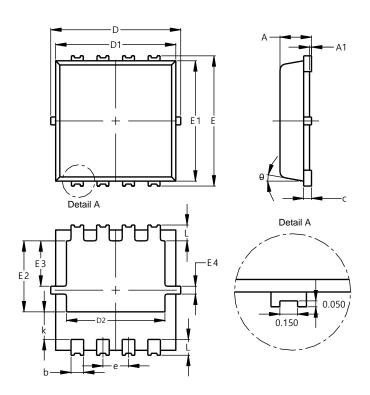
Figure 13. Transient Thermal Resistance



Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)

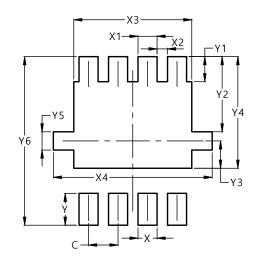


PowerDI3333-8/SWP					
(Type UX)					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05			
b	0.25	0.40	0.32		
C	0.10	0.25	0.15		
D	3.20	3.40	3.30		
D1	2.95	3.15	3.05		
D2	2.30	2.70	2.50		
E	3.20	3.40	3.30		
E1	2.95	3.15	3.05		
E2	1.60	2.00	1.80		
E3	0.95	1.35	1.15		
E4	0.10	0.30	0.20		
е	_	_	0.65		
k	0.50	0.90	0.70		
L	0.30	0.50	0.40		
θ	0°	12°	10°		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8/SWP (Type UX)



Dimensions	Value (in mm)				
С	0.650				
Х	0.420				
X1	0.420				
X2	0.230				
Х3	2.600				
X4	3.500				
Υ	0.700				
Y1	0.550				
Y2	1.650				
Y3	0.600				
Y4	2.450				
Y5	0.400				
Y6	3.700				



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